

In The Drawings

A new Figure 3A is now being prepared to show the third insulating material layer recited in claim 15. The new Figure 3A will be submitted under separate cover.

Regarding the comments that the figures showing cross-sectional views of the claimed invention are not properly cross-hatched, the Applicants respectfully submit a copy of the cross-hatching guidelines showing the correct usage of the cross-hatching lines for metal, i.e. an electrically conductive layer 14.

In The Specification

Paragraph beginning at line 5 of page 21 through page 22, line 10, has been amended as follows:

Figure 2A illustrates an enlarged, cross-sectional view of a present invention structure 10 similar to that of Figure 1G, but on an insulating layer 12. A plane view of the electronic structure 10 is shown in Figure 2B. The versatility of the present invention process for forming electronic structures with in-situ formed unit resistors 24 is thus shown in Figures 2A and 2B. For

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instance, to form a unit resistor that has a single resistance value of $1R$, the structure shown on the left side of Figure 2B can be utilized which includes a conductive element 28 with node D1 electrically connected to a single electrically resistive via 24 and a conductive element 16 with a node D2. The circuit shown on the right side of Figure 2B indicates that a resistance value of $2R$ can be obtained between the conductive element 30 with anode D3 and the conductive element 42 by flowing an electrical current through via 34 to metal 32, and from metal 32 via 36 to metal 42 which has two resistive vias connected in-series. Via 34 and via 36 are connected in-series by conductive element 44. The resistance value obtained between the conductive element 30 and the conductive element 42 or to node D5 therefore doubles that obtained between the conductive element 28 and the conductive element 16. Similarly, by connecting via 36 and via 38 in-series by the conductive element 42, and then connecting via 38 to metal 48 or node D6 to have an electrical resistance of $3R$. Furthermore, metal 30 or from node D3 through vias 34, 36, 38 and 40 in-series by the conductive element 46, or node D7, an electrical resistance of $4R$ may be obtained between the conductive element 30 and the conductive element 46. A versatile electrically resistive